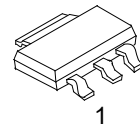


**UFZT958**

Preliminary

PNP SILICON TRANSISTOR**PNP SILICON PLANAR HIGH
CURRENT
(HIGH PERFORMANCE)
TRANSISTORS****■ FEATURES**

- * 0.5 Amp continuous current
- * Up to 1.5 Amps peak current
- * Very low saturation voltage
- * Excellent gain characteristics specified up to 1 Amp



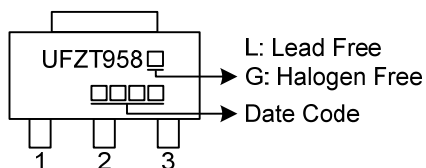
SOT-223

■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UFZT958L-AA3-R	UFZT958G-AA3-R	SOT-223	B	C	E	Tape Reel

Note: Pin Assignment: B: Base C: Collector E: Emitter

UFZT958G-AA3-R	(1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AA3: SOT-223 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING

■ **ABSOLUTE MAXIMUM RATINGS** ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	-400	V
Collector-Emitter Voltage		V_{CEO}	-400	V
Emitter-Base Voltage		V_{EBO}	-7	V
Collector Current	DC	I_C	-0.5	A
	Pulse(Note2)	I_{CP}	-1.5	A
Collector Dissipation		P_C	1.6	W
Junction Temperature		T_J	-55 ~ +150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **THERMAL DATA**

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	78	$^{\circ}\text{C/W}$

Note: Device mounted on FR-4 substrate P_c board, 2oz copper, with 1inch square copper plate.

■ **ELECTRICAL CHARACTERISTICS** ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-100μA	-400			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-10mA (Note)	-400			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-100μA	-6			V
Collector Cut-off Current	I _{CBO}	V _{CB} =-300V			-50	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} =-6V			-10	nA
ON CHARACTERISTICS						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-10mA, I _B =-1mA (Note)			-150	mV
		I _C =-100mA, I _B =-10mA (Note)			-200	mV
		I _C =-500mA, I _B =-100mA (Note)			-400	mV
Base -Emitter Saturation Voltage	V _{BE(SAT)}	I _C =-500mA, I _B =-100mA (Note)			-950	mV
Base-Emitter On Voltage	V _{BE(ON)}	I _C =-500mA, V _{CE} =-10V			-840	mV
DC Current Gain	h _{FE}	I _C =-10mA, V _{CE} =-10V	100			
		I _C =-500mA, V _{CE} =-10V	100		300	
		I _C =-1A, V _{CE} =-10V	10			
SMALL-SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	I _C =-100mA, V _{CE} =-10V, f=50MHz		85		MHz

Note: Measured under pulsed conditions. Pulse width = 300ms. Duty cycle $\leq 2\%$.

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